

## P-Channel Enhancement Mode Field Effect Transistor

### General Description

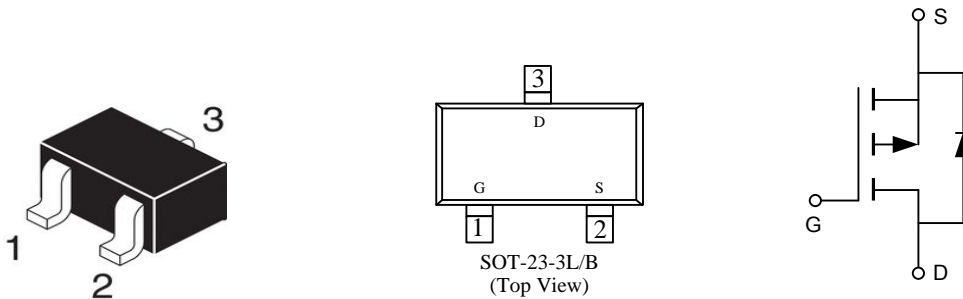
Product Summary		
$V_{DSS}$	$I_D$	$R_{DS(ON)}(m\Omega)TYP$
-20V	-0.45A	135 @ $V_{GS}=-4.5V$
	-0.35A	180 @ $V_{GS}=-2.5V$

### Features

- Super high dense cell design for low  $R_{DS(ON)}$
- Rugged and reliable
- Simple drive requirement
- SOT-23-3L/B package

### Package

- SOT-23-3L/B



### Ordering Information

Part Number	Storage Temperature	Package	Devices Per Reel
PN2305	-55°C to +150°C	SOT-23-3L/B	3000

### Absolute Maximum Ratings

( $T_A=25^\circ C$  unless otherwise noted)

parameter	symbol	limit	unit	
Drain-source voltage	$V_{DSS}$	-20	V	
Gate-source voltage	$V_{GSS}$	$\pm 12$	V	
Coutinuous drain current ( $T_j=150^\circ C$ )	$I_D$	$T_A=25^\circ C$	-0.8	A
		$T_A=80^\circ C$	-0.7	A
Pulsed drain current	$I_{DM}$	-1.8	A	
Drain-source Diode forward current	$I_S$	-0.58	A	
Power dissipation	$P_D$	$T_A=25^\circ C$	0.27	W
		$T_A=70^\circ C$	0.16	
Operating junction Temperature range	$T_j$	-55—150	$^\circ C$	